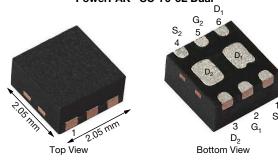


Vishay Siliconix

Dual P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A)	Q _g (TYP.)						
-20	0.054 at V _{GS} = -4.5 V	-4.5 ^a							
	0.070 at V _{GS} = -2.5 V	-4.5 ^a	9.5 nC						
	0.104 at V _{GS} = -1.8 V	-1.8 V -4.5 ^a							
	0.165 at V _{GS} = -1.5 V	-1.5							

PowerPAK® SC-70-6L Dual



Marking Code: DP **Ordering Information:**

SiA923AEDJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

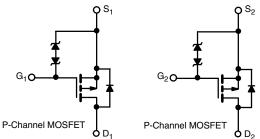
- TrenchFET® Power MOSFET
- Thermally Enhanced PowerPAK® SC-70 Package
 - Small Footprint Area
 - Low On-Resistance
- Typical ESD Protection: 2500 V
- 100 % R_q Tested
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



FREE

APPLICATIONS

- Charger Switches and Load Switches for Portable Devices
- DC/DC Converters



PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V _{DS}	-20	V		
Gate-Source Voltage		V _{GS}	± 8	v		
	T _C = 25 °C		-4.5 ^a			
Continuous Drain Current (T. 150 °C)	T _C = 70 °C		-4.5 ^a			
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	I _D	-4.5 a,b,c			
	T _A = 70 °C		-4.5 a,b,c	А		
Pulsed Drain Current (t = 100 μs)		I _{DM}	-15			
0 " 0 5 5 5 4 0 4	T _C = 25 °C	,	-4.5 ^a			
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	-1.6 ^{b,c}			
	T _C = 25 °C		7.8			
Marian and Danier Disable at	T _C = 70 °C	D	5	14/		
Maximum Power Dissipation	T _A = 25 °C	P _D	1.9 ^{b,c}	W		
	T _A = 70 °C		1.2 b,c			
Operating Junction and Storage Temperature R	T _J , T _{stg}	-55 to 150	°C			
Soldering Recommendations (Peak Temperatur	e) d,e		260			

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum Junction-to-Ambient b,f $t \le 5 s$		R_{thJA}	52	65	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	12.5	16	C/ VV				

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: Manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 110 °C/W.

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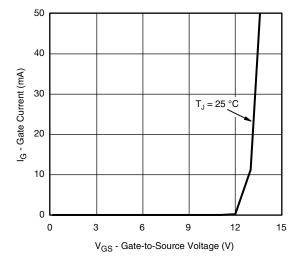
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT				
Static				•						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-20	-	-	V				
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	J 050 A	-	-15	-	mV/°C				
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = -250 μA	-	2.5	-					
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.4	-	-0.9	V				
Cata Cauraa Laakaga		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$	-	± 0.3	± 3	μΑ				
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$	-	± 3	± 30					
Zoro Coto Voltogo Droin Current		V _{DS} = -20 V, V _{GS} = 0 V	-	-	-1					
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$	-		-10					
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-15	-	-	Α				
		$V_{GS} = -4.5 \text{ V}, I_D = -3.8 \text{ A}$	-	0.044	0.054					
Drain-Source On-State Resistance a	D	$V_{GS} = -2.5 \text{ V}, I_D = -3.3 \text{ A}$	-	0.057	0.070	Ω				
Diain-Source On-State nesistance	R _{DS(on)}	$V_{GS} = -1.8 \text{ V}, I_D = -1 \text{ A}$	-	0.075	0.104					
		$V_{GS} = -1.5 \text{ V}, I_D = -0.5 \text{ A}$	-	0.097	0.165	<u>l</u>				
Forward Transconductance ^a	9 _{fs}	$V_{DS} = -10 \text{ V}, I_{D} = -3.8 \text{ A}$	-	11	-	S				
Dynamic ^b										
Input Capacitance	C _{iss}		-	770	=					
Output Capacitance	Coss	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	90	-	pF				
Reverse Transfer Capacitance	C _{rss}		-	81	-					
Total Gate Charge	0	$V_{DS} = -10 \text{ V}, V_{GS} = -8 \text{ V}, I_D = -4.9 \text{ A}$	-	16.3	25	nC				
Total date onlinge	Q_g		-	9.5	14.5					
Gate-Source Charge	Q_{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4.9 \text{ A}$	-	1.4	-					
Gate-Drain Charge	Q_{gd}		-	2.3	-					
Gate Resistance	R _g f = 1 MHz		1	5.1	10	Ω				
Turn-On Delay Time	t _{d(on)}		-	15	25					
Rise Time	t _r	V_{DD} = -10 V, R_L = 2.6 Ω	-	16	25	ns				
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -3.9 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$	-	30	45					
Fall Time	t _f		-	10	15					
Turn-On Delay Time	t _{d(on)}		-	7	15					
Rise Time	t _r	t_r $V_{DD} = -10 \text{ V, R}_L = 2.6 \Omega$		12	20					
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -3.9 \text{ A}, V_{GEN} = -8 \text{ V}, R_g = 1 \Omega$	-	26	40					
Fall Time	t _f		-	10	15					
-	Drain-Source Body Diode Characteristics									
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	-	-	-4.5	A				
Pulse Diode Forward Current	I _{SM}		-	-	-15					
Body Diode Voltage	V_{SD}	$I_S = -3.9 \text{ A}, V_{GS} = 0 \text{ V}$	-	-0.9	-1.2	V				
Body Diode Reverse Recovery Time	t _{rr}		-	13	25	ns				
Body Diode Reverse Recovery Charge	Q _{rr}	l _F = -3.9 A, dl/dt = 100 A/μs, T _J = 25 °C	-	5.5	12	nC				
Reverse Recovery Fall Time	t _a	i _F = 0.0 Λ, απαι = 100 Λ/μο, 1 _J = 25 0	-	7.5	-	no				
Reverse Recovery Rise Time	t _b		-	5.5	-	ns				

Notes

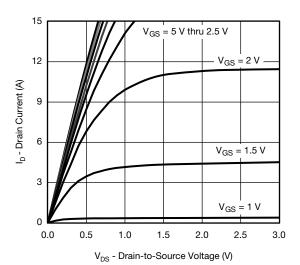
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

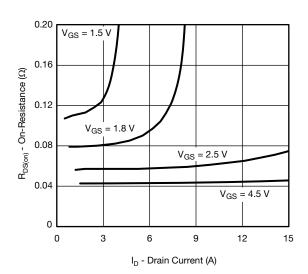




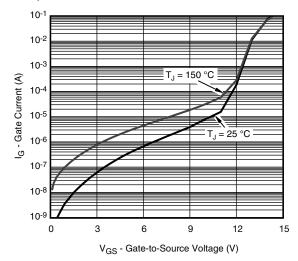
Gate Current vs. Gate-to-Source Voltage



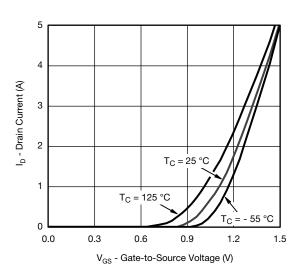
Output Characteristics



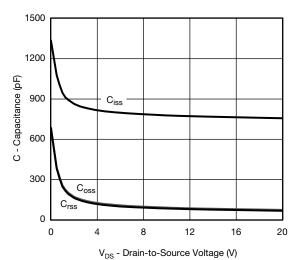
On-Resistance vs. Drain Current and Gate Voltage



Gate Current vs. Gate-to-Source Voltage

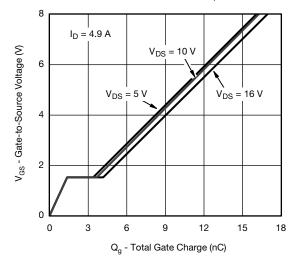


Transfer Characteristics

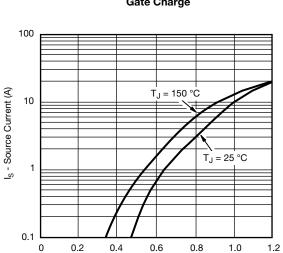


Capacitance

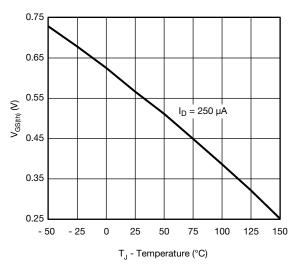




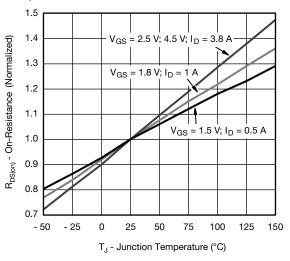
Gate Charge



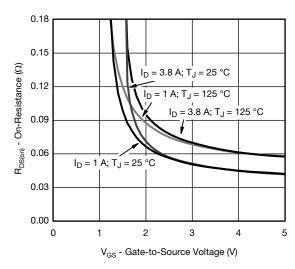
V_{SD} - Source-to-Drain Voltage (V) Source-Drain Diode Forward Voltage



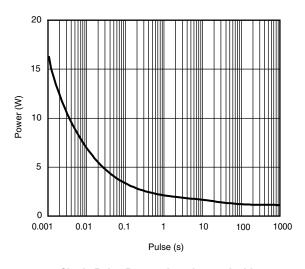
Threshold Voltage



On-Resistance vs. Junction Temperature

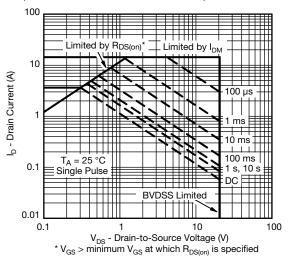


On-Resistance vs. Gate-to-Source Voltage

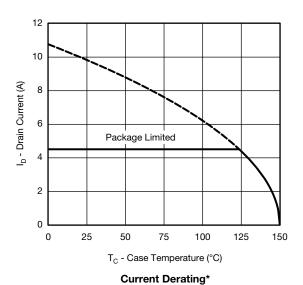


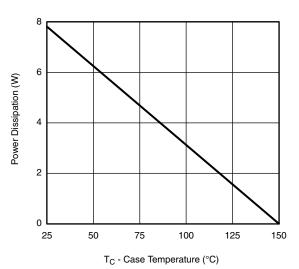
Single Pulse Power, Junction-to-Ambient





Safe Operating Area, Junction-to-Ambient

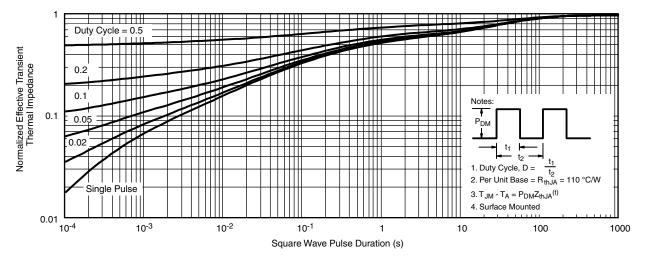




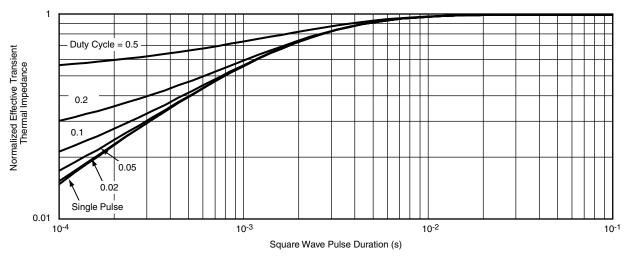
Power Derating

^{*} The power dissipation P_D is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg262936.

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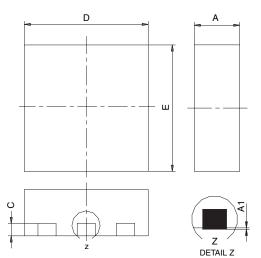
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

	SINGLE PAD						DUAL PAD						
DIM	M	ILLIMETER	RS	INCHES			MILLIMETERS			INCHES			
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028	
D2	0.135	0.235	0.335	0.005	0.009	0.013							
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041	
E2	0.345	0.395	0.445	0.014	0.016	0.018							
E3	0.425	0.475	0.525	0.017	0.019	0.021							
е		0.65 BSC			0.026 BSC			0.65 BSC			0.026 BSC		
K		0.275 TYP	1		0.011 TYP	1	0.275 TYP		0.011 TYP				
K1		0.400 TYP	1		0.016 TYP			0.320 TYP		0.013 TYP			
K2		0.240 TYP	1	0.009 TYP			0.252 TYP		0.010 TYP				
К3		0.225 TYP	1	0.009 TYP									
K4		0.355 TYP	1	0.014 TYP									
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015	
Т							0.05	0.10	0.15	0.002	0.004	0.006	
FCN: C-07431 - Bey C. 06-Aug-07													

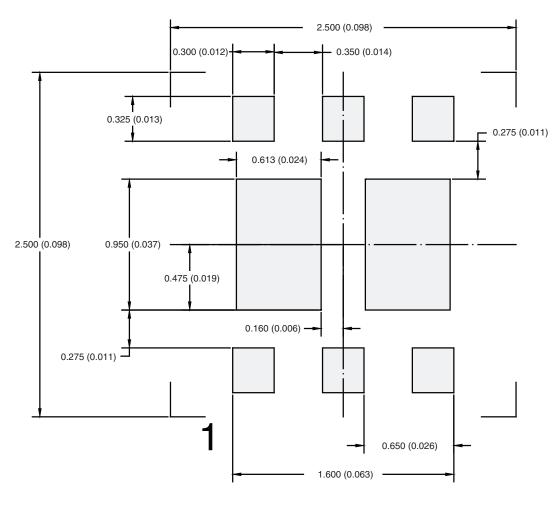
DWG: 5934

Document Number: 73001 06-Aug-07

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RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Dual



Dimensions in mm (inches)

Return to Index

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Vishay

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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

单击下面可查看定价,库存,交付和生命周期等信息

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